

GnP POLI - 762



I n t e l l i g e n t C M P S y s t e m F o r R e s e a r c h & D e v e l o p m e n t G & P T e c h n o l o g y

SPECIFICATIONS

- **Head, Table** 30 ~ 200rpm, Rotational motion, Head oscillation(± 12 mm)
- **Size** 1,580W 1,480D 1,960Hmm
- **Platen size** $\varnothing 762$ mm,(30inch), Teflon coated Aluminum
- **Pressing method** Variable air pressure electronic controller
 - Membrane Type : 70 ~ 350g/cm² (1psi ~ 5psi)
 - Wafer Down Force & Conditioning Load Monitoring System
- **Process** Automatic sequence, Dry - in / Wet - out

OPTIONS

- Pad Profile Measurement
- Friction Force & Temperature Monitoring System

APPLICATIONS

- **Workpiece** Max 12 inch wafer
- **CMP Process** Si CMP, Oxide CMP(BPSG, TEOS, ThOx), Metal CMP(W, Cu), STI, etc.

CHARACTERISTICS

- 300mm CMP Machine for R & D
- Stable repeatability(WTWN < 5%)
- High rigidity
- Wide application for CMP R & D